

N-Channel Power MOSFET

Description

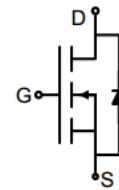
This is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies and adaptors.

General Features

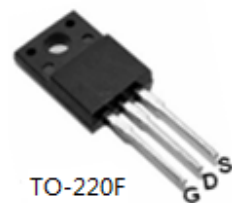
- V_{DS} 500V
- I_D (at $V_{GS} = 10V$) 9A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 0.85Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



Device	Package	Marking	Packaging
840	TO-220/220F	840	50pcs/Tube

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value		Units
		TO-220	TO-220F	
V_{DS}	Drain-Source Voltage	500		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	9.0	9.0*	A
	- Continuous ($T_C = 100^\circ\text{C}$)	5.4	5.4 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	36	36 *	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	360		mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.9		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	139	45.5	W
	- Derate above 25°C	1.11	0.36	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value		Units
		TO-220	TO-220F	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.90	2.75	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Electrical Characteristics

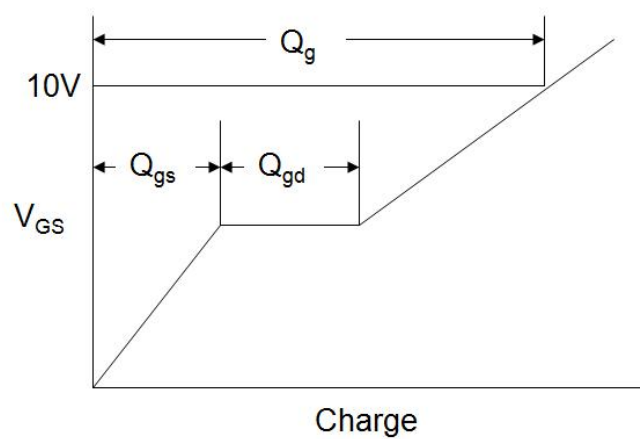
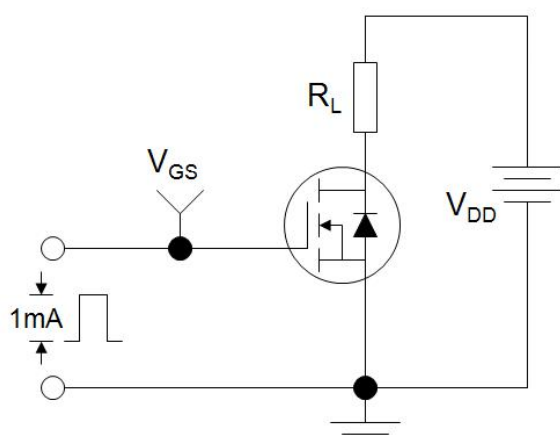
 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 400 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.5 A	--	0.65	0.85	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	870	--	pF
C _{oss}	Output Capacitance		--	130	--	pF
C _{rss}	Reverse Transfer Capacitance		--	25	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 9.0A, R _G = 25 Ω (Note 4, 5)	--	20	--	ns
t _r	Turn-On Rise Time		--	70	--	ns
t _{d(off)}	Turn-Off Delay Time		--	90	--	ns
t _f	Turn-Off Fall Time		--	60	--	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 9.0 A, V _{GS} = 10 V (Note 4, 5)	--	30	-	nC
Q _{gs}	Gate-Source Charge		--	4.0	--	nC
Q _{gd}	Gate-Drain Charge		--	15	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	9.0	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	36.0	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 9.0 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9.0 A, dI _F / dt = 100 A/μs (Note 4)	--	340	--	ns
Q _{rr}	Reverse Recovery Charge		--	3.0	--	μC

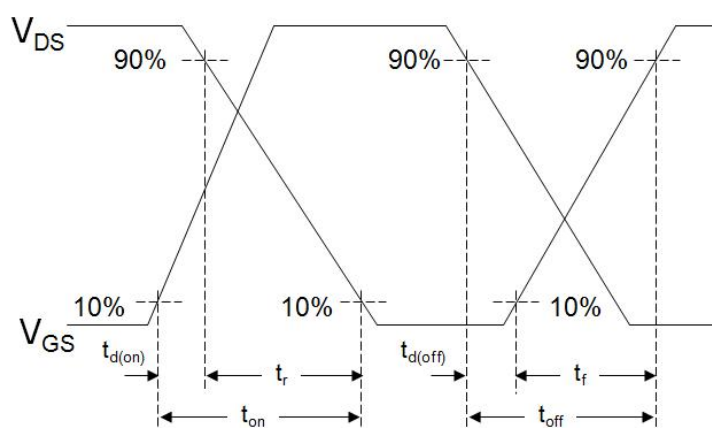
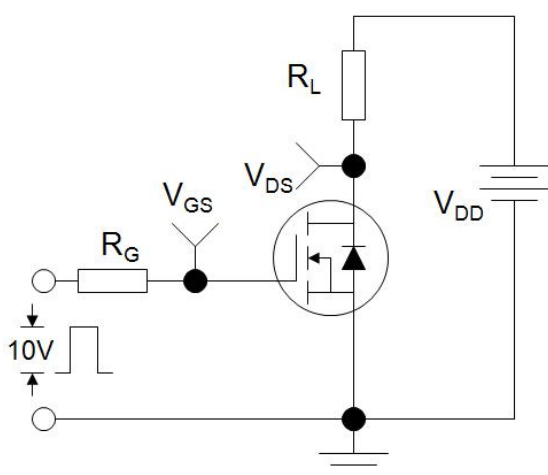
Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 8\text{ mH}, I_{AS} = 9.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9.0\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

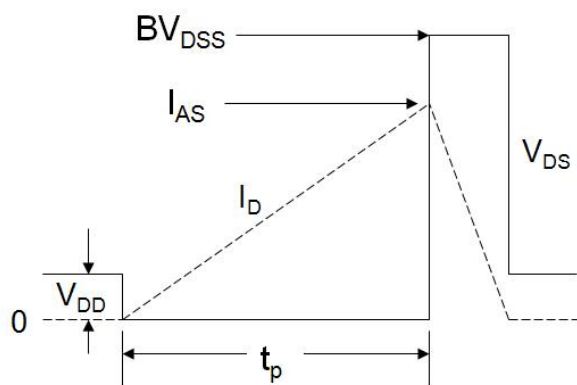
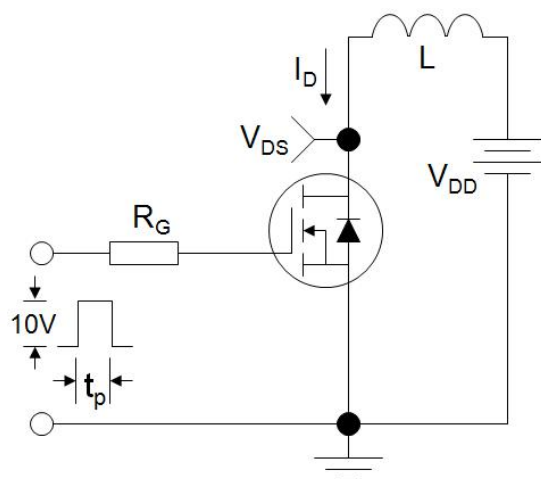
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics

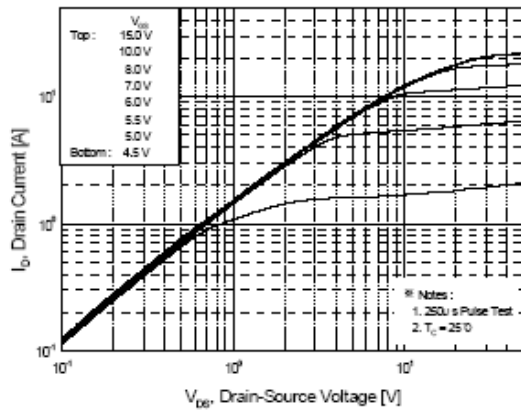


Figure 1. On-Region Characteristics

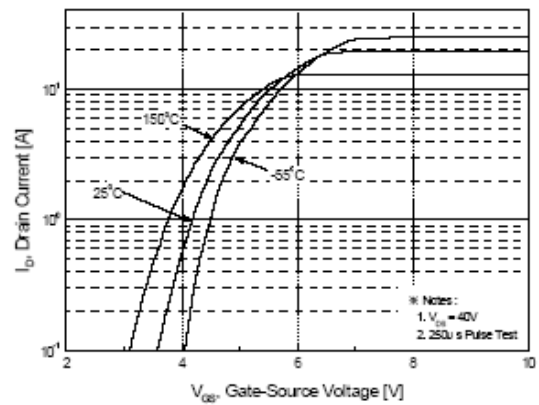


Figure 2. Transfer Characteristics

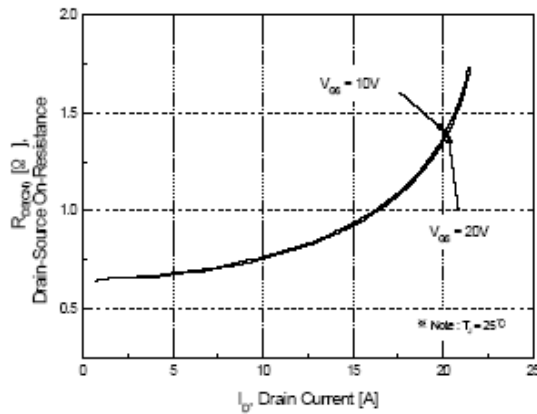


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

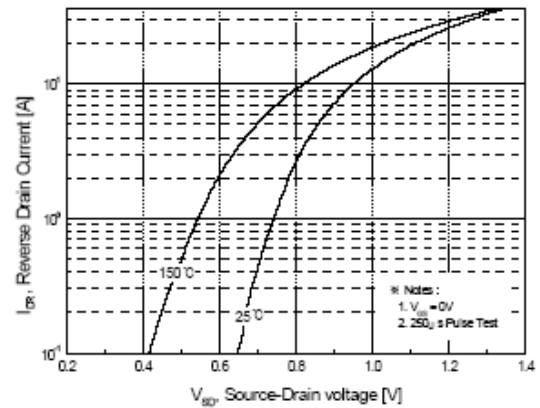


Figure 4. Body Diode Forward Voltage Variation with Source Current

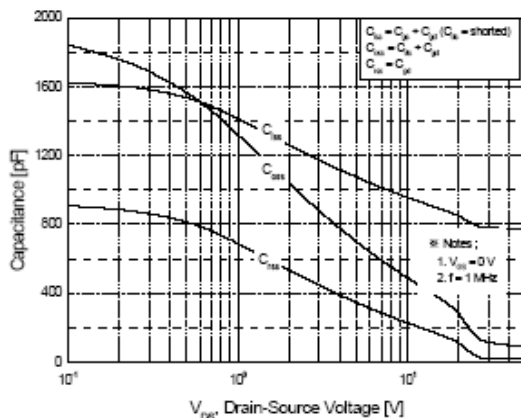


Figure 5. Capacitance Characteristics

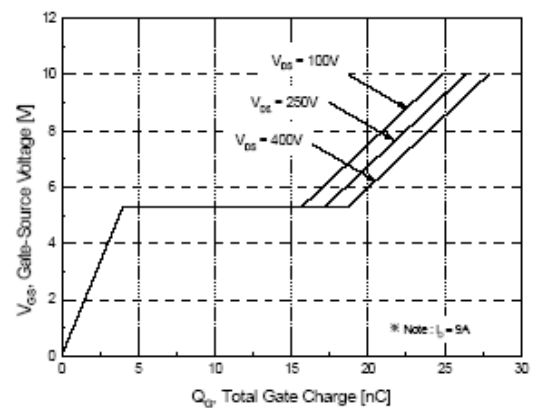


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

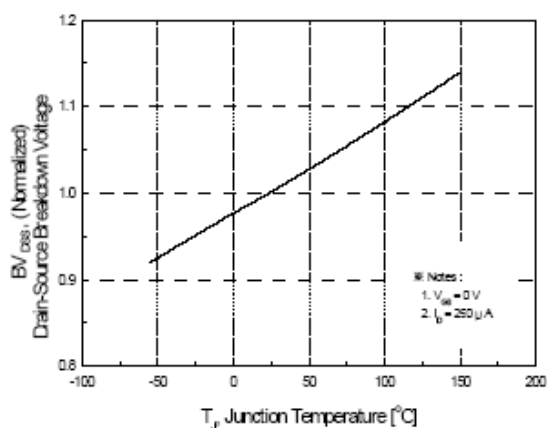


Figure 7. Breakdown Voltage Variation vs Temperature

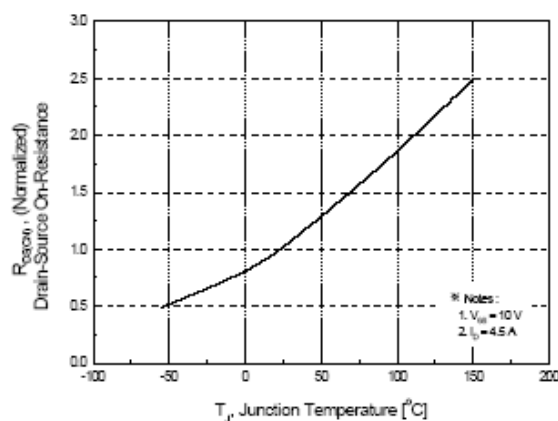


Figure 8. On-Resistance Variation vs Temperature

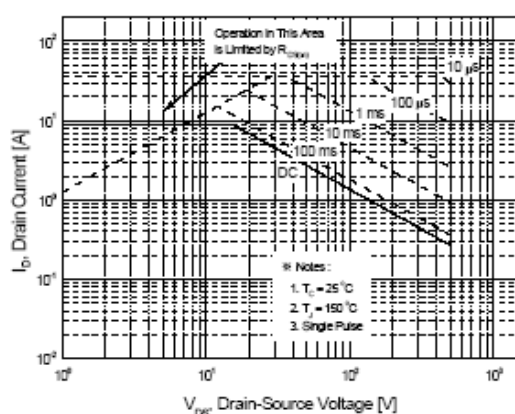


Figure 9-1. Maximum Safe Operating Area for SLP840C

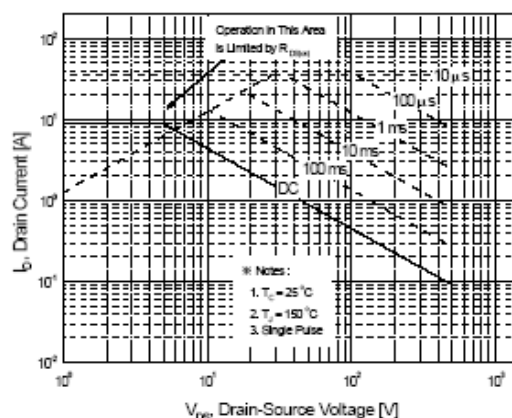


Figure 9-2. Maximum Safe Operating Area for SLF840C

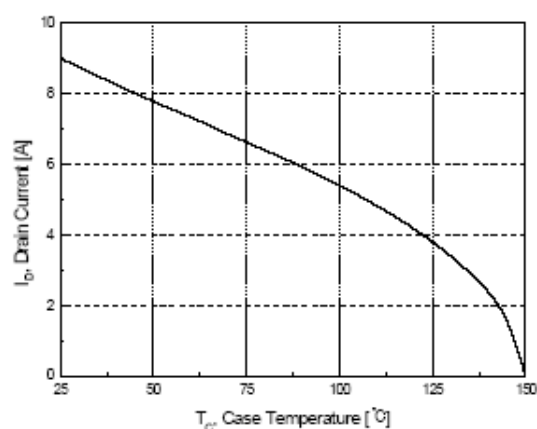


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

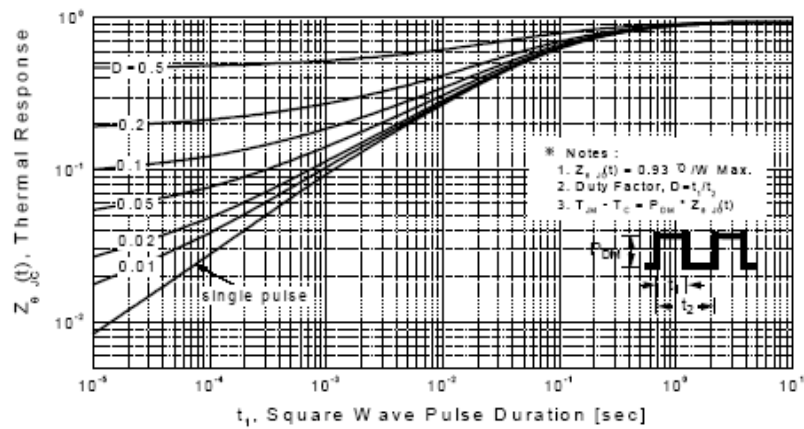
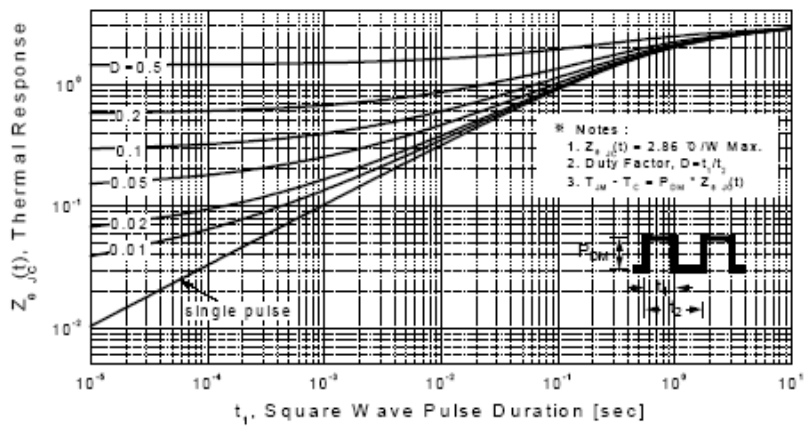
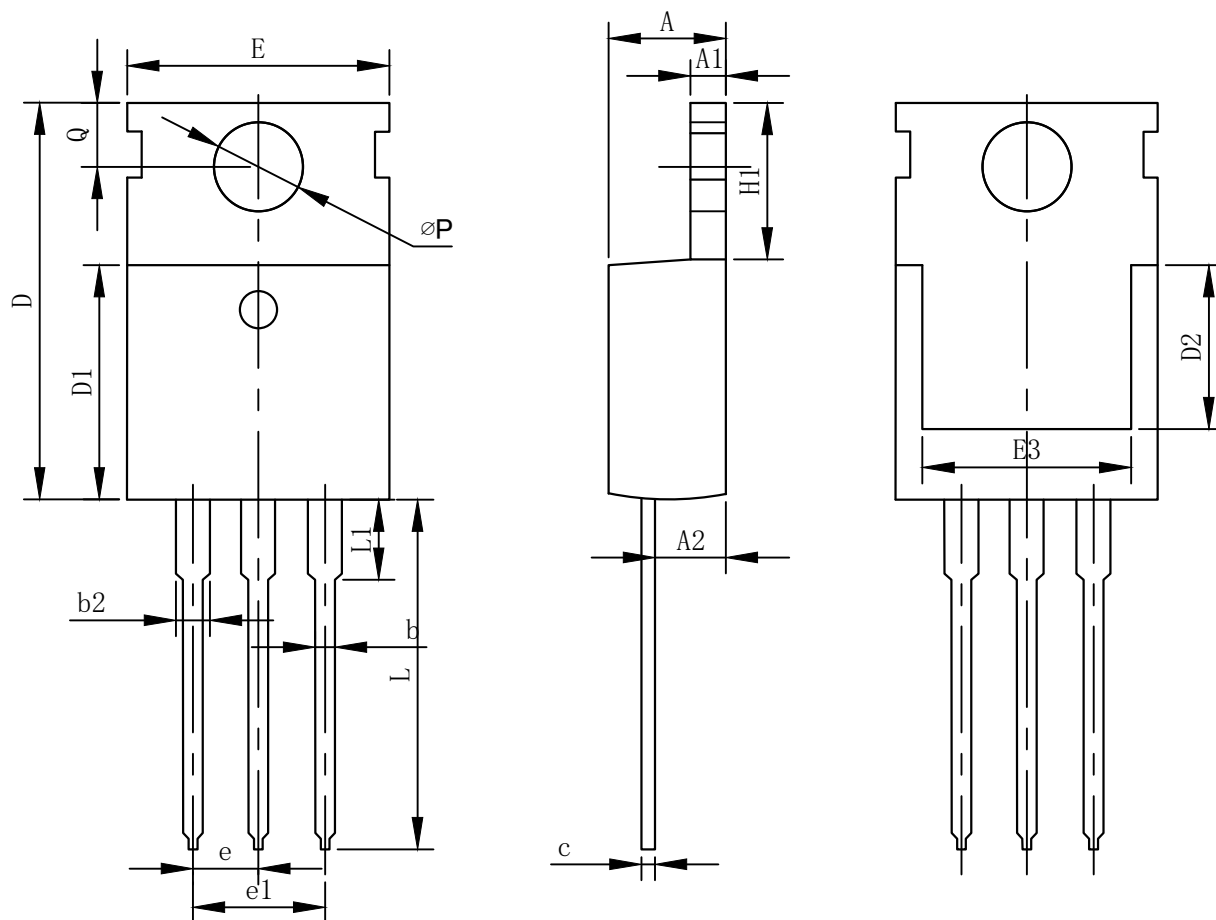


Figure 22-2. Transient Thermal Response Curve for SLP840C



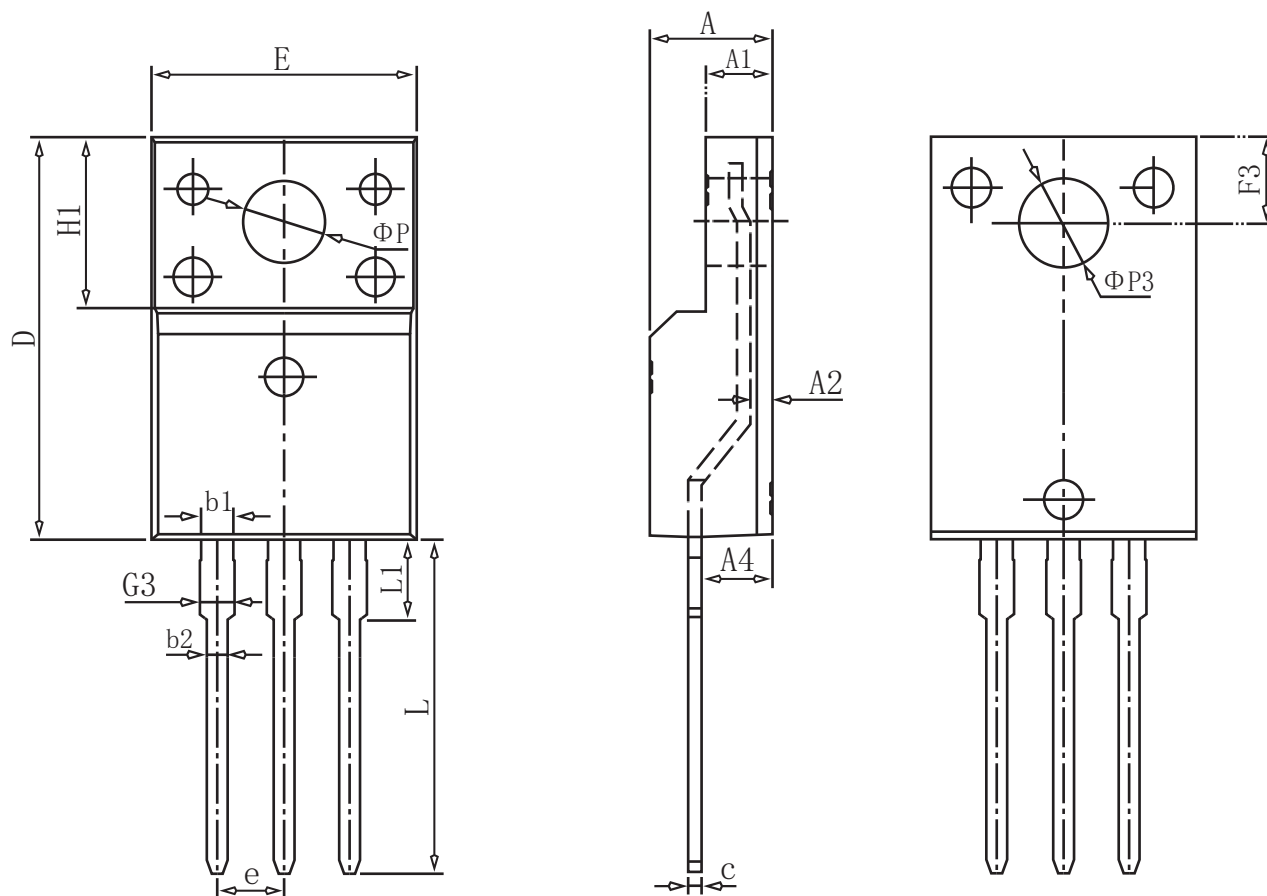
TO-220 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.70	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	—	—
E	9.70	10.00	10.30
E3	7.00	—	—
e	2.54BSC		
e1	5.08BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	—	3.10	3.40
$\varnothing P$	3.40	3.60	3.80
Q	2.60	2.80	3.00

TO-220F Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
E	10.00	10.20	10.40
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.65	0.85	1.30
A4	2.55	2.75	2.95
c	0.40	0.50	0.65
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
ΦP	3.183REF		
L	12.68	12.98	13.28
L1	3.25	3.45	3.65
$\Phi P3$	3.45REF		
F3	3.10	3.30	3.50
G3	1.10	1.30	1.50
b1	1.05	1.20	1.35
b2	0.70	0.80	0.92